

PERFORMANCE SPECIFICATION SHEET

SEMICONDUCTOR DEVICE, DIODE, NON-HERMETIC, EPOXY, SURFACE MOUNT, SILICON,
BIDIRECTIONAL TRANSIENT VOLTAGE SUPPRESSOR, TYPES 1N6036AUEG THROUGH
1N6072AUEG, 1N6036AUEJ THROUGH 1N6072AUEJ, JAN, JANTX, AND JANTXV

This specification is approved for use by all Departments
and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of
this specification sheet and MIL-PRF-19500.

1. SCOPE

1.1 Scope. This specification covers the performance requirements for non-hermetic, epoxy, surface mount 1,500 watt, bi-directional silicon transient voltage suppressor diodes. Three levels of product assurance are provided for each device as specified in MIL-PRF-19500.

1.2 Physical dimensions. See figure 1 (surface mount).

1.3 Maximum ratings. Maximum ratings are as shown in maximum test ratings (see 3.7) and as follows:

$P_{PP} = 1500 \text{ W}$ (see figures 2 and 3) at $t_p = 1.0 \text{ ms}$.

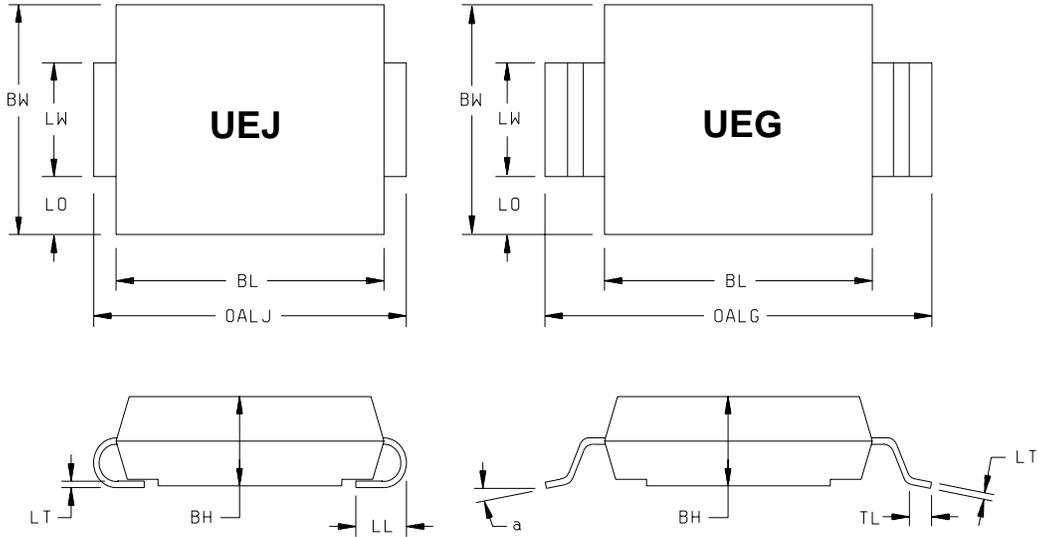
$P_{M(AV)} = 1.0 \text{ W}$ (derate at $8 \text{ mW/}^\circ\text{C}$ above $T_A = +25^\circ\text{C}$) (see 6.4).

$I_{FSM} = 200 \text{ A (pk)}$ at $t_p = 8.3 \text{ ms}$ ($T_A = +25^\circ\text{C}$).

$-55^\circ\text{C} \leq T_{OP} \leq +150^\circ\text{C}$ (ambient), $-55^\circ\text{C} \leq T_{STG} \leq +150^\circ\text{C}$ (ambient).

1.4 Primary electrical characteristics at $T_A = +25^\circ\text{C}$. Primary ratings are as shown in maximum test ratings (see 3.8).

Comments, suggestions, or questions on this document should be addressed to Defense Supply Center, Columbus, ATTN: DSCC-VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to semiconductor@dsc.dla.mil. Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <http://assist.daps.dla.mil>.



Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
BH	.075	.103	1.91	2.62	
BL	.260	.280	6.60	7.11	
BW	.220	.245	5.59	6.22	
LL	.030	.060	0.76	1.52	
LT	.006	.012	0.15	0.30	
LW	.108	.124	2.74	3.15	
OALG	.380	.400	9.65	10.16	
OALJ	.305	.320	7.75	8.13	
TL	.025	.040	.635	1.02	
a		10°		10°	

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. UEG indicates Gull-Wing lead configuration; UEJ indicates a J-Lead configuration.
4. UEG and UEJ are not to be marked on device.
5. In accordance with ASME Y14.5M, measurements are equivalent to Φ x symbology.

FIGURE 1. Physical dimensions.

2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3, 4, or 5 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3, 4, or 5 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATIONS

MIL-PRF-19500 - Semiconductor Devices, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-750 - Test Methods for Semiconductor Devices.

(Copies of these documents are available online at <http://assist.daps.dla.mil/quicksearch/> or <http://assist.daps.dla.mil/> or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2.2 Non-Government publications. The following document forms a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

JESD22-A102 - Accelerated Moisture Resistance - Unbiased Autoclave.

(Application for copies should be addressed to: JEDEC Solid State Technology Association 2000, 2500 Wilson Boulevard, Arlington VA 22201-3834 <http://www.jedec.org/>.)

2.3 Order of precedence. In the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 General. The individual item requirements shall be as specified in MIL-PRF-19500 and as modified herein.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturers list before contract award (see 4.2 and 6.3).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500 and as follows.

3.4 Interface and physical dimensions. The interface and physical dimensions shall be as specified in MIL-PRF-19500, and on figure 1.

3.4.1 Metallurgically bonded construction. Metallurgically bonded construction is required. The bonding flow shall have flow points above 260°C.

3.4.2 Lead finish. Lead finish shall be solderable in accordance with MIL-PRF-19500, MIL-STD-750, and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see 6.2).

3.5 Marking. Devices shall be marked in accordance with MIL-PRF-19500. For surface mount devices, the minimum marking shall be PIN (1N and UEG or UEJ may be omitted), manufacturer's name, trademark, or identification or manufacturer's designating symbol, lot identification code, and code for plants. All marking which is omitted from the body of the device shall appear on the label of the initial container.

3.6 Electrical performance characteristics. Unless otherwise specified, the electrical performance characteristics are as specified in 1.3, 1.4, and tables I, II, and IV.

3.7 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table I herein.

3.8 Maximum test ratings and primary electrical characteristics. Maximum ratings shall be in accordance with columns 5 through 8 of table IV. Primary electrical characteristics are as shown in columns 2 and 4 of table IV.

3.9 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.4).

4.1.1 Sampling and inspection. Sampling and inspection shall be in accordance with MIL-PRF-19500 and as specified herein except lot accumulation shall be 3-months in lieu of 6 weeks.

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500 and as specified herein.

4.2.1 Group E qualification. Group E inspection shall be performed for qualification or requalification only. In case qualification was awarded to a prior revision of the associated specification that did not request the performance of table III tests, the tests specified in table III herein shall be performed on the first inspection lot of this revision to maintain qualification.

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4.3 Screening (JANTX and JANTXV levels only). Screening shall be in accordance with table IV of MIL-PRF-19500, and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see table IV of MIL-PRF-19500)	Measurement
	JANTX and JANTXV level
3a	T _(high) = +150°C
7, 9, 10, 11	Not applicable
12	See 4.3.1
13	Interim electrical, delta, and table I, subgroups 2 and 3, electrical parameters not applicable for this screen (performed in screen 12).
14	Not required

4.3.1 Power burn-in (HTRB) and steady-state operation life test conditions. The test conditions and order of events shall be as follows:

- a. Pulse in accordance with 4.5.2.a, in polarity A 10 times (screening and group B) and 50 times (group C) at $T_A = +25^\circ\text{C}$.
- b. Pulse in accordance with 4.5.2.a, in polarity B 10 times (screening and group B) and 50 times (group C) at $T_A = +25^\circ\text{C}$.
- c. Read I_D in polarities A and B at $T_A = +25^\circ\text{C}$, remove defective devices and record the number of failures.
- d. Apply the working peak reverse voltage (V_{WM}) (column 4 of table IV) at polarity A at $T_A = +125^\circ\text{C}$ as follows:
 - (1) For 96 hours (JANTX and JANTXV) for the screening test.
 - (2) For 340 hours (JANTX and JANTXV) for group B steady-state operation life test.
 - (3) For 1000 hours for group C steady-state operation life test.
- e. Read I_D in polarity A at $T_A = +25^\circ\text{C}$. Devices with $\Delta I_D > 50$ percent (100 percent for steady-state operation life) of the initial reading or $1 \mu\text{A}$ dc, whichever is greater shall be considered defective. Remove defective devices and record the number of failures (see note).
- f. Apply the working peak reverse voltage (V_{WM}) (column 4 of table IV) at polarity B at $T_A = +125^\circ\text{C}$ as follows:
 - (1) For 96 hours (JANTX and JANTXV) for the screening test.
 - (2) For 340 hours (JANTX and JANTXV) for group B steady-state operation life test.
 - (3) For 1000 hours for group C steady-state operation life test.
- g. Read I_D in polarity B at $T_A = +25^\circ\text{C}$. Devices with $\Delta I_D > 50$ percent (100 percent for steady-state operation life) of the initial reading or $1 \mu\text{A}$ dc, whichever is greater shall be considered defective. Remove defective devices and record the number of failures (see note).
- h. Read V_{BR} in polarities A and B at $T_A = +25^\circ\text{C}$. Devices with $\Delta V_{BR} > 2$ percent (± 5 percent for steady-state operation life) of the initial reading shall be considered defective. Remove defective devices and record the number of failures (see note).
- i. Read I_D in polarity A at $T_A = +25^\circ\text{C}$, remove defective devices and record the number of failures.

NOTE: For the purpose of this test, the direction in which the device is first pulsed shall be considered polarity A and the reverse direction polarity B.

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with MIL-PRF-19500 and table I herein. End-point electrical measurements shall be in accordance with table I, subgroup 2 herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VIb (JAN, JANTX and JANTXV) of MIL-PRF-19500. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of table II herein.

4.4.2.1 Group B inspection, table VIb (JAN, JANTX and JANTXV) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Conditions</u>
B2	1051	-55°C to +150°C.
B2	JESD22-A102	Hermetic seal not applicable; autoclave, 96 hours, 121°C, 30 psig.
B2	4066	Condition for surge, 1 cycle, see 4.5.3.
B3	1027	See 4.5.1 and 4.5.2.
B5	Not applicable.	

NOTE: All electrical measurements and tests shall be performed twice, once in each direction.

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VII of MIL-PRF-19500. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of table II herein.

4.4.3.1 Group C inspection, table VII of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Conditions</u>
C2	Not applicable	
C3	JESD22-A102 1051	Autoclave: Condition C, 96 hours Temperature cycle: Condition B, 100 cycles
	JESD22-A102 1051	Autoclave: Condition C, 96 hours Temperature cycle: Condition B, 100 cycles.
C5	Not applicable	
C6	1026	See 4.5.1 and 4.5.2.
C7	Condition for temperature coefficient of breakdown voltage are as follows: I_{BR} = column 3 of table IV, $T_1 = +25^\circ\text{C} \pm 3^\circ\text{C}$, $T_2 = T_1 + 100^\circ\text{C}$; $n = 22$, $c = 0$.	
C8	Condition for maximum peak pulse current are as follows: See 4.5.2.b, (20 μs pulse only) 10 pulses; $n = 22$, $c = 0$.	

NOTE: All electrical measurements and tests shall be performed twice, once in each direction.

4.4.4 Group E inspection. Group E inspection shall be conducted in accordance with the conditions specified for subgroup testing in appendix E, table IX of MIL-PRF-19500 and as specified in table III herein. Electrical measurements (end-points) shall be in accordance with table I, subgroup 2 herein. See table II for delta limits when applicable.

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables as follows.

NOTE: For the purpose of this test, the direction in which the device is first pulsed shall be considered polarity A and the reverse direction polarity B.

4.5.1 Group C steady-state operation life test (alternate procedure). When the group B, 340 hour life test is continued on test to 1,000 hours to satisfy the group C life test requirements, the test shall be performed as given in 4.3.1 with the following exceptions: Step 4.3.1.d shall be repeated at the end of the 1,000 hours.

4.5.2 Maximum peak pulse current (I_{pp}). The peak pulse currents specified in column 7 of table IV shall be applied while simultaneously maintaining a bias voltage of not less than the applicable voltage specified in column 4 of table IV, in the same polarity as the peak pulse current. The peak pulse current shall be applied with a current vs time waveform as follows (1 pulse per minute maximum):

- a. Pulse current shall reach 100 percent of I_{pp} at $t \leq 10 \mu\text{s}$ and decay to 50 percent of I_{pp} at $t \geq 1 \text{ ms}$ for $t_p = 1 \text{ ms}$ (see figure 4).
- b. Pulse current shall reach 100 percent of I_{pp} at $t \leq 8 \mu\text{s}$ and decay to 50 percent of I_{pp} at $t \geq 20 \mu\text{s}$ for (see figure 5).

4.5.3 Clamping voltage. The peak pulse clamping voltage shall be measured across the diode in a 1 ms time interval. The response detector shall demonstrate equipment accuracy of ± 3 percent. The peak clamping voltage as specified in column 6 of table IV shall be applicable to the 1 ms pulse of 4.5.2.a only.

TABLE I. Group A inspection.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits <u>2/</u>		Unit
	Method	Conditions <u>2/</u>		Min	Max	
<u>Subgroup 1</u> Visual and mechanical examination	2071					
<u>Subgroup 2 3/</u> Standby current	4016	DC method, $V_R = V_{WM}$ (column 4 of table IV)	I_D		Column 5	μA dc
Breakdown voltage	4022	$t_p \leq 300$ ms, duty cycle ≤ 2 percent, $I_{BR} =$ column 3 of table IV	V_{BR}	Column 2	Column 2	V dc
<u>Subgroup 3 3/</u> Low temperature operation: Minimum breakdown voltage	4022	$T_A = -55^\circ C$ $t_p \leq 300$ ms, duty cycle ≤ 2 percent, $I_{BR} =$ column 3 of table IV	V_{BR}	Column 10		V dc
High temperature operation: Reverse current leakage	4016	$T_A = 125^\circ C$ DC method, $V_R = V_{WM}$, column 4 of table IV	I_{D2}		Column 9	mA dc
<u>Subgroup 4 3/</u> Clamping voltage maximum (pulsed) (see 4.5.3)		$t_p = 1.0$ ms (see 4.5.2.b), $I_{PP} =$ column 7 of table IV	V_C		Column 6	V (pk)
<u>Subgroup 5, 6 and 7</u> Not applicable						

1/ For sampling plan, see MIL-PRF-19500.

2/ Column references are to table IV.

3/ All electrical testing shall be performed twice, once in each direction.

TABLE II. Groups B and C electrical and delta measurements. 1/ 2/ 3/

Step	Inspection	MIL-STD-750		Symbol	Limits 4/		Unit
		Method	Conditions 4/		Min	Max	
1.	Standby current	4016	DC method, $V_R = V_{WM}$ column 4 of table IV	I_D		Column 5	μA dc
2.	Breakdown voltage	4022	$t_p \leq 300$ ms, duty cycle ≤ 2 percent, $I_{BR} =$ column 3 of table IV	V_{BR}	Column 2	Column 2	V dc
3.	Standby current	4016	DC method; $V_R = V_{WM}$ (column 4 of table IV)	ΔI_D 5/		100 percent of initial reading or 20 percent of column 5 of table I, whichever is greater.	
4.	Breakdown voltage	4022	$t_p \leq 300$ ms, duty cycle ≤ 2 percent, $I_{BR} =$ column 3 of table IV	ΔV_{BR} 5/		± 5 percent of initial value	
5.	Clamping voltage		$t_p = 1.0$ ms (see 4.5.2.b); $I_{PP} =$ column 7 of table IV	V_C		Column 6	V (pk)

1/ All electrical testing shall be performed twice, once in each direction.

2/ The electrical measurements for table VIb of MIL-PRF-19500 are as follows:

- a. Subgroup 2, see table II herein, steps 1 and 2.
- b. Subgroup 6 see table II herein, steps 1, 2, 3 and 4.

3/ The electrical measurements for table VII of MIL-PRF-19500 are as follows:

- a. Subgroup 2 and 3, see table II herein, steps 1 and 2.
- b. Subgroup 9, see table II herein, steps 1 and 2 for all levels.

4/ Column references are to table IV.

5/ Devices which exceed the group A limits for this test shall not be accepted.

TABLE III. Group E inspection (all quality levels) for qualification only.

Inspection	MIL-STD-750		Sampling plan
	Method	Conditions	
<u>Subgroup 1</u>	1051	500 cycles, condition C, -55°C to +150°C.	45 devices c = 0
Temperature cycling			
Electrical measurements		See table II, steps 1, 2, 3, 4, and 5.	
<u>Subgroup 2</u>		1,000 hours. See 4.3.1.	22 devices c = 0
Life test			
Electrical measurements		See table II, steps 1, 2, 3, 4, and 5.	
<u>Subgroups 4 and 5</u>			
Not applicable			
<u>Subgroup 6</u>			
Peak pulse current		See 4.5.2. Ipp shall be characterized by the supplier and this data shall be available to the government. Test shall be performed on each low and high voltage device for each structurally identical grouping. Test to failure.	
Electrical measurements		See table II, steps 1, 2, 3, 4, and 5.	

TABLE IV. Characteristics and ratings.

Col 1	Col 2		Col 3	Col 4	Col 5	Col 6	Col 7		Col 8	Col 9	Col 10	Col 11
Type	Breakdown voltage		Test current I _{BR}	Working peak reverse voltage V _{WM}	Maximum standby current I _D	Maximum clamping voltage V _C at I _{pp}	Maximum peak pulse current (I _{pp})		Maximum temperature coefficient of V _{BR} αV _{BR}	Maximum standby current I _D T _A = +125°C	Minimum breakdown voltage at I _{BR} T _A = -55°C	Breakdown current I _{BR} maximum dc current T _A = +25°C
	Min V dc	Max V dc					t _p = 20 μs t _r = 8 μs	t _p = 1 ms t _r = 10 μs				
	Min V dc	Max V dc	mA dc	V (pk)	μA dc	V (pk)	A (pk)	A (pk)	%/°C	μA dc	V dc	mA dc
1N6036A	7.13	7.88	10	6.0	1000	11.3	750	132.0	0.061	2000	6.66	125.0
1N6037A	7.79	8.61	10	7.0	500	12.1	700	124.0	0.065	1000	7.24	115.0
1N6038A	8.65	9.55	10	7.5	200	13.4	630	112.0	0.068	400	8.01	104.0
1N6039A	9.50	10.50	1	8.5	50	14.5	585	103.0	0.073	200	8.75	95.0
1N6040A	10.50	11.60	1	9.0	10	15.6	545	96.0	0.075	200	9.65	86.0
1N6041A	11.40	12.60	1	10.0	5	16.7	510	90.0	0.078	200	10.40	73.0
1N6042A	12.40	13.70	1	11.0	5	18.2	465	82.0	0.081	200	11.30	70.0
1N6043A	14.30	15.80	1	12.0	5	21.2	400	71.0	0.084	200	13.00	63.0
1N6044A	15.20	16.80	1	13.0	5	22.5	375	67.0	0.086	200	13.70	59.0
1N6045A	17.10	18.90	1	15.0	5	25.2	335	59.5	0.088		15.40	53.0
1N6046A	19.00	21.00	1	17.0	5	27.7	305	54.0	0.090	200	17.10	47.0
1N6047A	20.90	23.10	1	18.0	5	30.6	275	49.0	0.092	200	18.80	43.0
1N6048A	22.80	25.20	1	20.0	5	33.2	255	45.0	0.094	200	20.50	39.0
1N6049A	25.70	28.40	1	22.0	5	37.5	225	40.0	0.096	200	23.00	35.0
1N6050A	28.50	31.50	1	25.0	5	41.4	205	36.0	0.097	200	25.50	31.0
1N6051A	31.40	34.70	1	28.0	5	45.7	185	33.0	0.098	200	29.00	28.0
1N6052A	34.20	37.80	1	30.0	5	49.9	170	30.0	0.098	200	30.50	26.0
1N6053A	37.10	41.00	1	33.0	5	53.9	155	28.0	0.100	200	33.10	24.0
1N6054A	40.90	45.20	1	36.0	5	59.3	145	25.3	0.101	200	36.40	22.0
1N6055A	44.70	49.40	1	40.0	5	64.8	130	23.2	0.101	200	39.80	20.0

TABLE IV. Characteristics and ratings - Continued.

Col 1	Col 2		Col 3	Col 4	Col 5	Col 6	Col 7		Col 8	Col 9	Col 10	Col 11
Type	Breakdown voltage		Test current	Working peak reverse voltage	Maximum standby current	Maximum clamping voltage	Maximum peak pulse current (I _{PP})		Maximum temperature coefficient of V _{BR} αV _{BR}	Maximum standby current I _D T _A = +125°C	Minimum breakdown voltage at I _{BR} T _A = -55°C	Breakdown current I _{BR} maximum dc current T _A = +25°C
	V _{BR} at I _{BR}		I _{BR}	V _{WM}	I _D	V _C at I _{PP}	t _p = 20 μs t _r = 8 μs	t _p = 1 ms t _r = 10 μs				
	Min V dc	Max V dc	mA dc	V (pk)	μA dc	V (pk)	A (pk)	A (pk)	%/°C	μA dc	V dc	mA dc
1N6056A	48.50	53.60	1	43.0	5	70.1	120	21.4	0.102	200	43.10	18.0
1N6057A	53.20	58.80	1	47.0	5	77.0	110	19.5	0.103	200	47.30	17.0
1N6058A	58.90	68.20	1	53.0	5	85.0	100	17.7	0.104	200	52.30	15.0
1N6059A	64.60	71.40	1	58.0	5	92.0	90	16.3	0.104	200	57.30	14.0
1N6060A	71.30	78.80	1	64.0	5	103.0	82	14.6	0.105	200	63.20	12.0
1N6061A	77.90	86.10	1	70.0	5	113.0	75	13.3	0.105	200	69.00	11.0
1N6062A	86.50	95.50	1	75.0	5	125.0	68	12.0	0.106	200	76.50	10.0
1N6063A	95.00	105.00	1	82.0	5	137.0	62	11.0	0.106	200	84.10	9.5
1N6064A	105.00	116.00	1	94.0	5	152.0	55	9.9	0.107	200	92.80	8.5
1N6065A	114.00	126.00	1	100.0	5	168.0	50	8.9	0.107	200	100.00	7.5
1N6066A	124.00	137.00	1	110.0	5	182.0	47	8.2	0.107	200	109.00	7.0
1N6067A	143.00	158.00	1	128.0	5	213.0	40	7.0	0.108	200	126.00	6.0
1N6068A	162.00	179.00	1	145.0	5	245.0	36	6.1	0.108	200	143.00	5.5
1N6069A	171.00	189.00	1	150.0	5	261.0	34	5.7	0.108	200	151.00	5.2
1N6070A	181.00	200.00	1	160.0	5	278.0	32	5.4	0.108	200	157.00	5.0
1N6071A	190.00	210.00	1	170.0	5	294.0	30	5.1	0.108	200	169.00	4.7
1N6072A	209.00	231.00	1	185.0	5	328.0	25	4.6	0.108	200	184.00	4.3

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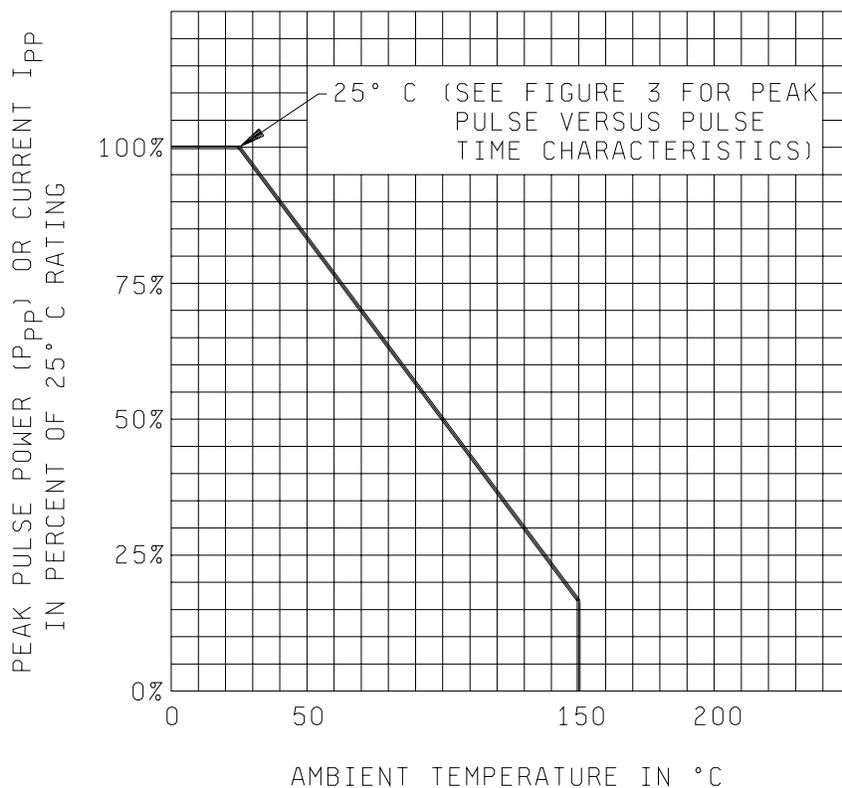


FIGURE 2. Derating curve.

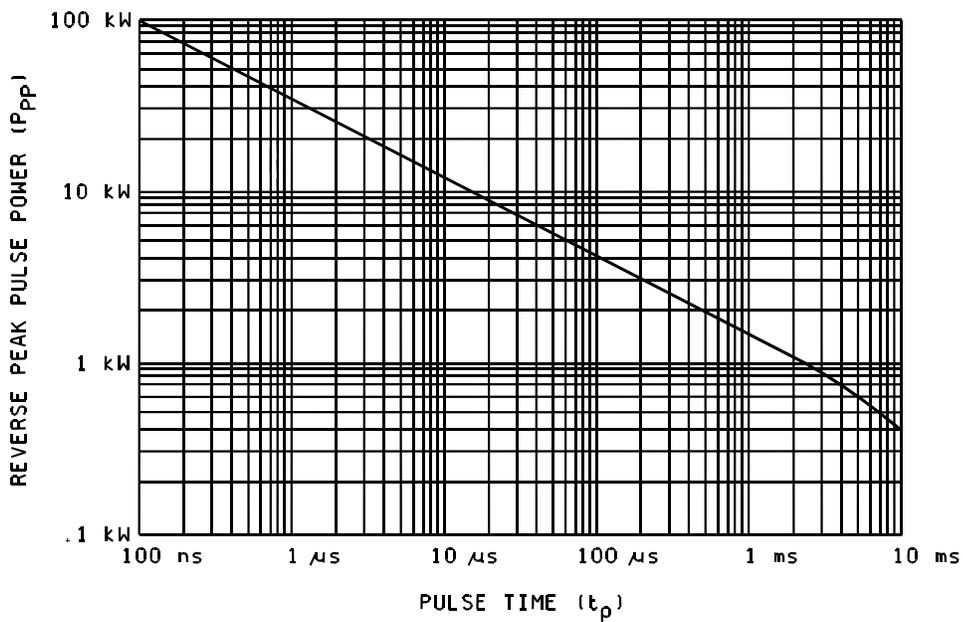
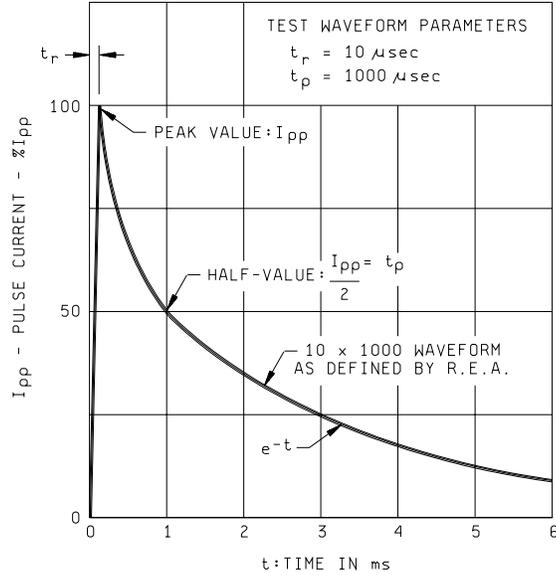
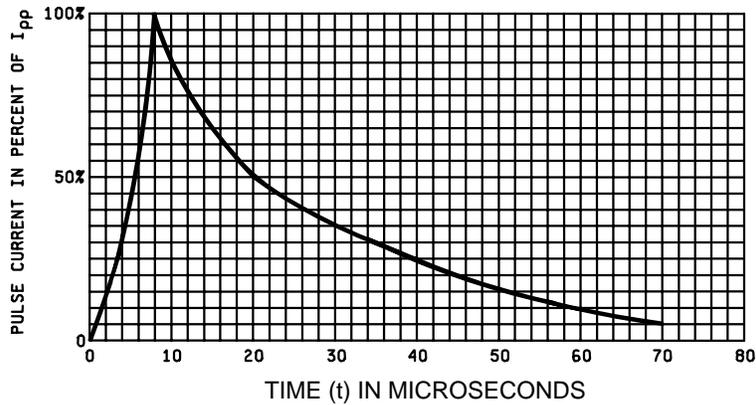


FIGURE 3. Peak pulse power versus pulse time.



NOTE: Pulse time duration is defined as that point where the pulse current decays to 50 percent of I_{pp} . (Rise time to 100 percent of $I_{pp} = 10 \mu\text{s}$).

FIGURE 4. Current impulse waveform (see 4.5.2.a).



NOTE: Pulse time duration is defined as that point where the pulse current decays to 50 percent of I_{pp} . (Rise time to 100 percent of $I_{pp} = 8 \mu\text{s}$).

FIGURE 5. Current impulse waveform (see 4.5.2.b).

5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activities within the Military Service or Defense Agency, or within the Military Service's system commands. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory.)

6.1 Intended use. The notes specified in MIL-PRF-19500 are applicable to this specification.

6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Title, number, and date of this specification.
- b. Packaging requirements (see 5.1).
- c. Lead finish (see 3.4.1).
- d. Product assurance level and type designator.

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List (QML-19500) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from Defense Supply Center, Columbus, ATTN: DSCC/VQE, P.O. Box 3990, Columbus, OH 43218-3990 or e-mail vqe.chief@dla.mil.

6.4 Steady state power rating. This rating is not relevant for most applications.

6.5 Thermal impedance and thermal resistance. Since there is no temperature sensitive parameter, thermal impedance and thermal resistance cannot be measured.

Custodians:
Army - CR
Navy - EC
Air Force - 11
NASA - NA
DLA - CC

Preparing activity:
DLA - CC

(Project 5961-2707)

Review activities:
Army - MI
Navy - AS, SM
Air Force - 19, 99

NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at <http://assist.daps.dla.mil/>.